

KSA952**PNP SILICON TRANSISTOR**

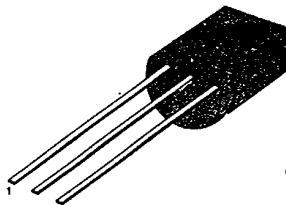
GENERAL PURPOSE APPLICATIONS
HIGH TOTAL POWER DISSIPATION
(PT=600 mW)

High h_{FE} and LOW $V_{CE(sat)}$

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-700	mA
Base Current	I_B	-150	mA
Collector Dissipation	P_C	600	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

TO-92



1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
*Base Emitter Voltage	V_{BE}	$V_{CE}=-6\text{V}, I_C=-10\text{mA}$	-600	-640	-700	mV
Collector Cutoff Current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-100	nA
*DC Current Gain	h_{FE1}	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	90	200	400	
	h_{FE2}	$V_{CE}=-1\text{V}, I_C=-700\text{mA}$	50	100		
*Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-700\text{mA}, I_B=-70\text{mA}$		-0.25	-0.6	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-700\text{mA}, I_B=-70\text{mA}$		-0.95	-1.2	V
Output Capacitance	C_{ob}	$V_{CB}=-6\text{V}, I_E=0, f=1\text{MHz}$			17	pF
Current Gain Bandwidth Product	f_T	$V_{CE}=-6\text{V}, I_E=10\text{mA}$	50	160		MHz

* Pulse test: $PW \leq 350\mu\text{s}$, duty cycle $\leq 2\%$ Pulsed

 h_{FE1} CLASSIFICATION

Classification	R	O	Y
h_{FE1}	90-180	135-270	200-400